# **BLP7G22-10**

# LDMOS driver transistor

Rev. 1 — 13 February 2012

Objective data sheet

### 1. Product profile

### 1.1 General description

The BLP7G22-10 is low power driver using NXP's state of the art GEN7 LDMOS technology. This device is perfectly suited as general purpose driver in the frequency range from 700 MHz to 2200 MHz.

Table 1. Application performance (multiple frequencies)

Typical RF performance at  $T_{case} = 25$  °C;  $I_{Dq} = 50$  mA; in a class-AB application circuit.

Test signal	f	I <sub>Dq</sub>	$V_{DS}$	P <sub>L(AV)</sub>	Gp	$\eta_D$	IMD3	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)	(dBc)
1-carrier W-CDMA	748	110	28	0.7	27	16	_	-45 <mark>[1]</mark>
	748	110	28	2	27	26	_	-43
2-carrier W-CDMA	2140	90	28	0.7	17	16	-46	-48 <mark>[2]</mark>
	2140	90	28	2	17	26	-40	-43

<sup>[1]</sup> Single carrier; Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.7 dB at 0.01 % probability on CCDF per carrier.

#### 1.2 Features and benefits

- Typical 1-carrier W-CDMA performance at frequency 748 MHz:
  - ◆ Average output power = 0.7 W
  - ◆ Power gain = 27 dB
  - ◆ Efficiency = 16 %
  - ◆ Ruggedness at least 10 : 1, P<sub>L</sub> = 10 W
- Typical 2-carrier W-CDMA performance at frequency 2140 MHz:
  - ◆ Average output power = 0.7 W
  - ◆ Power gain = 17 dB
  - Efficiency = 16 %
  - ◆ Ruggedness at least 10 : 1, P<sub>L</sub> = 10 W
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- Designed for broadband operation (700 MHz to 2200 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)



<sup>[2]</sup> Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF per carrier. Carrier spacing 10 MHz

**LDMOS** driver transistor

## 1.3 Applications

- GSM/EDGE
- TDS/CDMA
- W-CDMA

## 2. Pinning information

Table 2. Pinning

100000 =1	9		
Pin	Description	Simplified outline	Graphic symbol
1, 6, 7, 12	n.c.	40 7	0.0.40.44
2, 3, 4, 5	gate	12 7	8, 9, 10, 11
8, 9, 10, 11	drain		2, 3, 4, 5
13	source	[1]	13
		<u> </u>	aaa-002121
		Transparent top view	

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BLP7G22-10	HVSON12	plastic thermal enhanced very thin small outline package; no leads; 12 terminals; body 4 x 6 x 0.85 mm	SOT1179-1			

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{\text{th(j-c)}}$	transient thermal impedance from junction to case	$T_{case} = 70  ^{\circ}C;  P_{L} = 2  W$	3.0	K/W

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### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.18 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 18 \text{ mA}$	1.4	<tbd></tbd>	2.4	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 28 \text{ V};$ $I_D = \langle \text{tbd} \rangle \text{ mA}$	<tbd></tbd>	<tbd></tbd>	<tbd></tbd>	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	3.5	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	280	nΑ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 18 \text{ mA}$	107	160	210	mS
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 630 \text{ mA}$	0.32	0.79	1.26	mΩ

Table 7. RF characteristics

Test signal: 1-tone pulsed;  $t_p$  = 20  $\mu$ s;  $\delta$  = 10 %;  $f_1$  = 2110 MHz;  $f_2$  = 2170 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = <tbd><mA;  $T_{case}$  = 25  $^{\circ}$ C; unless otherwise specified, in a production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	1-tone pulsed; $P_{L(AV)} = 2 W$	<tbd></tbd>	17	<tbd></tbd>	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 2 W$	<tbd></tbd>	25	-	%
RLin	input return loss	$P_{L(AV)} = 2 W$	-	<tbd></tbd>	<tbd></tbd>	dB

### 6.1 Ruggedness in class-AB operation

The BLP7G22-10 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 110 mA;  $P_{L}$  = 10 W; frequency from 700 MHz to 2200 MHz.

## 7. Package outline

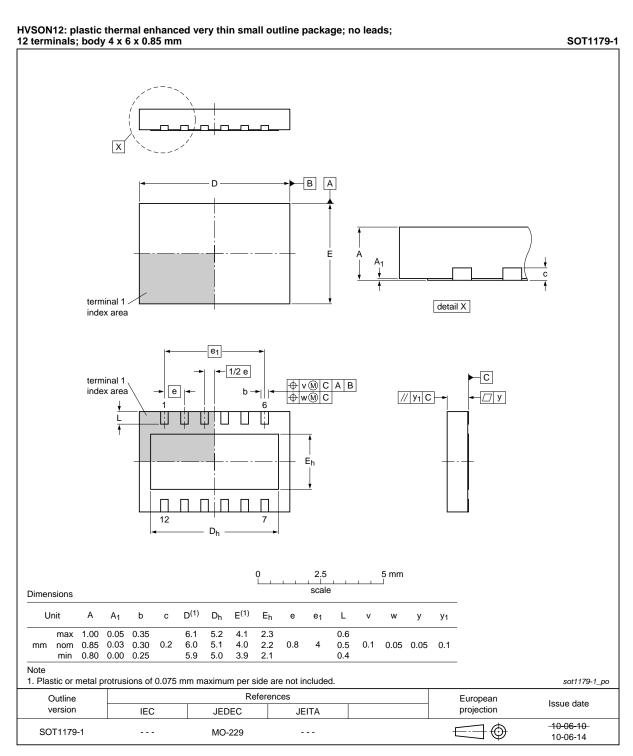


Fig 1. Package outline SOT1179-1

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## 8. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 9. Abbreviations

Table 8. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
DPCH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
GEN7	seventh-generation
GSM	Global System for Mobile Communication
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
TDS	Time Division Synchronous
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP7G22-10 v.1	20120213	Objective data sheet	-	-

### 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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